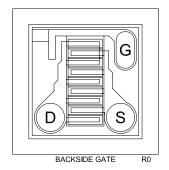


CP664V-2N2608

P-Channel JFET Die

The CP664V-2N2608 is a silicon P-Channel JFET designed for low level amplifier applications.



MECHANICAL SPECIFICATIONS:

Die Size	19 x 19 MILS
Die Thickness	7.9 MILS
Drain Bonding Pad Size	4.2 MILS DIAMETER
Source Bonding Pad Size	4.2 MILS DIAMETER
Gate Bonding Pad Size	2.9 x 5.3 MILS
Top Side Metalization	Al-Si – 17,000Å
Back Side Metalization	Au – 12,000Å
Scribe Alley Width	1.96 MILS
Wafer Diameter	5 INCHES
Gross Die Per Wafer	41,575

MAXIMUM RATINGS: (T _A =25°C) Drain-Gate Voltage	SYMBOL $V_{ extsf{DG}}$	30	UNITS V
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	30	V
Continuous Gate Current	I_{G}	50	mA
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 to +150	°C

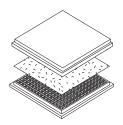
ELECTRICAL CHARACTERISTICS: (T _A =25°C unless otherwise noted)	ELECTRICAL	CHARACTERISTICS:	(T _△ =25°C unless o	therwise noted)
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SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _{GSS}	V_{GS} =5.0V, V_{DS} =0		10	nA
IDSS*	V_{DS} =5.0V, V_{GS} =0	0.9	4.5	mA
BV_{GSS}	I _G =1.0μA	30		V
V _{GS(OFF)}	V_{DS} =5.0V, I_{D} =1.0 μ A	1.0	4.0	V
y _{fs}	V_{DS} =5.0V, V_{GS} =0, f=1.0kHz	1.0K		μS
C _{iss}	V_{DS} =5.0V, V_{GS} =1.0V, f=140kHz		17	pF
NF	V_{DS} =5.0V, V_{GS} =0, f=1kHz,			
	R _G =1.0MΩ, BW=1.0Hz		3.0	dB

^{*}Pulse width < 100msec, Duty cycle <10%

BARE DIE PACKING OPTIONS

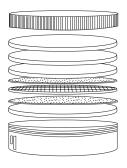




BARE DIE IN TRAY (WAFFLE) PACK

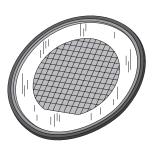
CT: Singulated die in tray (waffle) pack.
(example: CP211-PART NUMBER-CT)

CM: Singulated die in tray (waffle) pack 100% visually inspected as per MIL-STD-750, (method 2072 transistors, method 2073 diodes). (example: CP211-PART NUMBER-CM)



UNSAWN WAFER

WN: Full wafer, unsawn, 100% tested with reject die inked. (example: CP211-PART NUMBER-WN)



SAWN WAFER ON PLASTIC RING

WR: Full wafer, sawn and mounted on plastic ring, 100% tested with reject die inked.

(example: CP211-PART NUMBER-WR)

Please note: Sawn Wafer on Metal Frame (WS) is possible as a special order. Please contact your Central Sales Representative at 631-435-1110.



Visit the Central website for a complete listing of specifications: www.centralsemi.com/bdspecs

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- · Inventory bonding
- · Consolidated shipping options

- · Custom bar coding for shipments
- · Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free guick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- · Custom electrical curves
- · Environmental regulation compliance
- · Customer specific screening
- · Up-screening capabilities

- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- · Application and design sample kits
- · Custom product and package development

REQUESTING PRODUCT PLATING

- 1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
- 2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

Corporate Headquarters & Customer Support Team

Central Semiconductor Corp. 145 Adams Avenue Hauppauge, NY 11788 USA

Main Tel: (631) 435-1110 Main Fax: (631) 435-1824

Support Team Fax: (631) 435-3388

www.centralsemi.com

Worldwide Field Representatives: www.centralsemi.com/wwreps

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